

2SB1251

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Silicon PNP epitaxial planar type Darlington

For power amplification

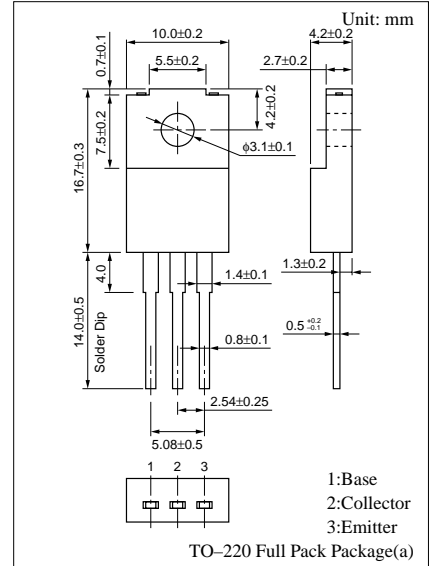
Complementary to 2SD1891

Features

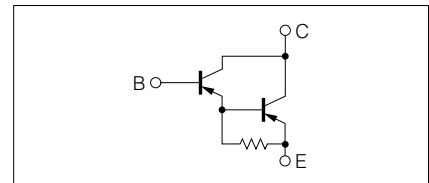
- Optimum for 30W HiFi output
- High forward current transfer ratio h_{FE} : 5000 to 30000
- Low collector to emitter saturation voltage $V_{CE(sat)}$: $< -3.0V$
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	-110	V	
Collector to emitter voltage	V_{CEO}	-90	V	
Emitter to base voltage	V_{EBO}	-5	V	
Peak collector current	I_{CP}	-7	A	
Collector current	I_C	-4	A	
Collector power dissipation	P_C	$T_C=25^\circ C$	40	W
		$T_a=25^\circ C$	2	
Junction temperature	T_j	150	$^\circ C$	
Storage temperature	T_{stg}	-55 to +150	$^\circ C$	



Internal Connection



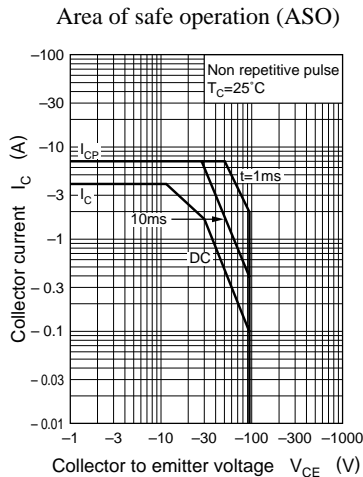
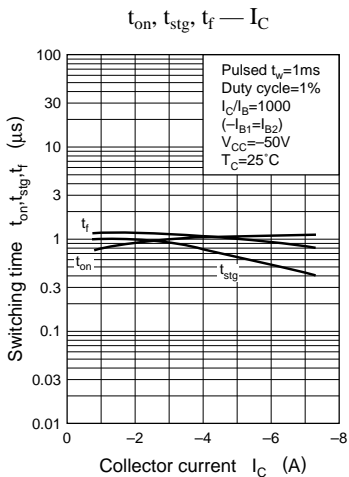
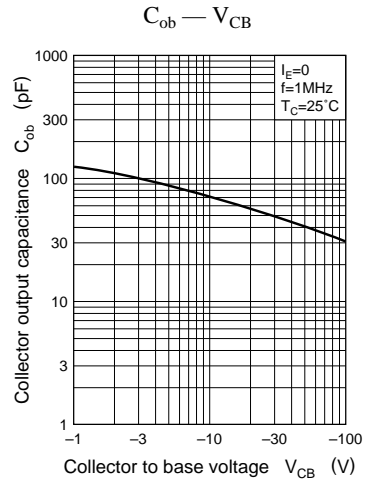
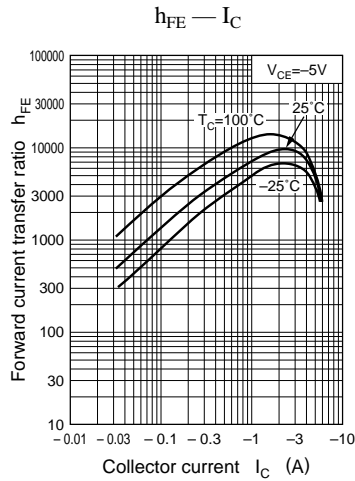
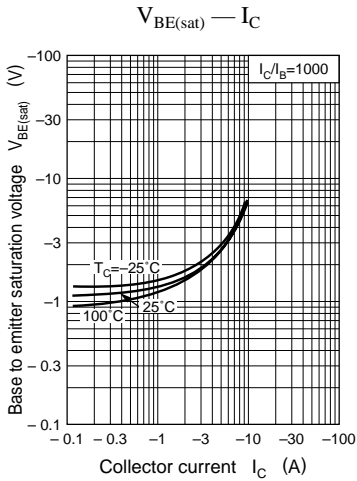
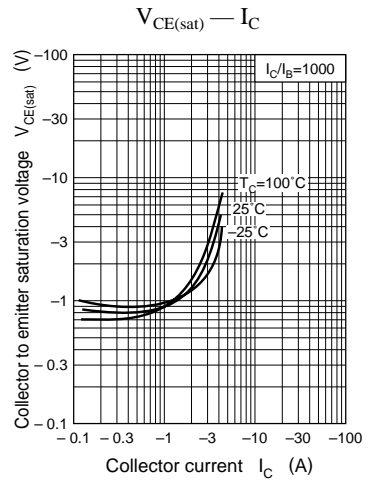
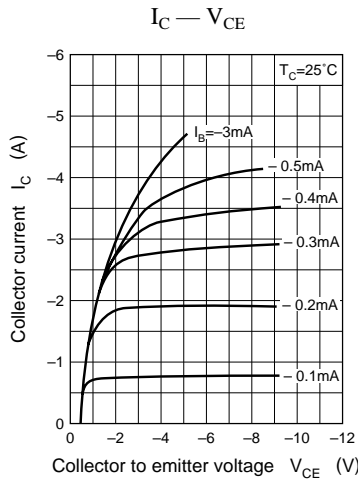
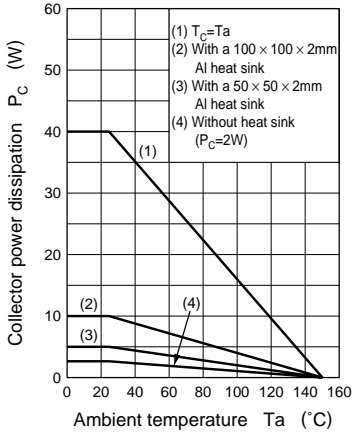
Electrical Characteristics ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -110V, I_E = 0$			-100	μA
	I_{CEO}	$V_{CE} = -90V, I_B = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	μA
Collector to emitter voltage	V_{CEO}	$I_C = -30mA, I_B = 0$	-90			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5V, I_C = -1A$	2000			
	h_{FE2}^*	$V_{CE} = -5V, I_C = -3A$	5000		30000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -3mA$			-3.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = -3mA$			-3.0	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -0.5A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = -2A, I_{B1} = -2mA, I_{B2} = 2mA, V_{CC} = -50V$		1.0		μs
Storage time	t_{stg}			0.8		μs
Fall time	t_f			1.0		μs

* h_{FE2} Rank classification

Rank	Q	P
h_{FE2}	5000 to 15000	8000 to 30000

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